

Amendments to the Claims:

This listing of claims will replace all prior versions, and listings of claims in the application:

Listing of Claims:

1 - 26. (Canceled)

1 27. (Currently amended): An electronic device comprising a semiconductor
2 device provided with pads and a substrate provided with pads on which said semiconductor
3 device is mounted, said pads of said semiconductor device being bonded to said pads of said
4 substrate through junctions ~~each including a Cu-Sn compound containing Cu₆Sn₅ and Cu balls~~
5 ~~comprising substantially of Cu, said Cu balls being formed by one or a mixture of an elemental~~
6 ~~Cu, a Cu alloy, and a Cu-containing compound, said Cu balls being bonded to each other by said~~
7 Cu₆Sn₅ comprising CuSn compounds and Cu balls, said CuSn compounds resulting from a
8 mixture of said Cu balls and an Sn-based solder subjected to a bonding operation at a
9 temperature above the melting point temperature of said Sn-based solder but less than the
10 melting point temperature of said Cu balls, wherein said Cu-Sn compound ~~further~~ includes
11 Cu₆Sn₅ and Cu₃Sn and said Cu₃Sn is disposed in a region between said Cu-balls and said Cu₆Sn₅.

28 and 29. (Canceled)

1 30. (Previously presented): An electronic device according to claim 27,
2 wherein said Cu₆Sn₅ has a thickness of about a few micrometers.

1 31. (Previously presented): An electronic device according to claim 27,
2 wherein said Cu₆Sn₅ is formed by reflowing said Cu-balls and Sn-base solder at a temperature
3 higher than a melting point of said Sn-base solder and lower than a melting point of said Cu-
4 balls.

1 32. (Previously presented): An electronic device according to claim 31,
2 wherein said Sn-base solder comprises eutectic Sn-Cu solder, eutectic Sn-Cu solder to which at

3 least one of In, Zn and Bi is added, eutectic Sn-Ag solder, eutectic Sn-Ag solder to which at least
4 one of In, Zn and Bi is added, eutectic Sn-Ag-Cu solder, or eutectic Sn-Ag-Cu solder to which at
5 least one of In, Zn and Bi is added.

1 33. (Previously presented): An electronic device according to claim 31,
2 wherein said Cu-balls have a diameter greater than 5 micrometers.

1 34. (Currently amended): An electronic device comprising a semiconductor
2 device provided with pads and a substrate provided with pads on which said semiconductor
3 device is mounted, said pads of said semiconductor device being bonded to said pads of said
4 substrate by way of junctions, each junction including a Cu-Sn compound containing Cu_6Sn_5 and
5 Cu_3Sn and Cu balls resulting from a mixture of said Cu balls and an Sn-based solder subjected to
6 a bonding operation at a temperature above the melting point temperature of said Sn-based solder
7 but less than the melting point temperature of said Cu balls ~~comprising substantially one or a~~
8 ~~mixture of elemental Cu, a Cu alloy, and a Cu compound, said Cu balls being bonded to each~~
9 ~~other by said Cu-Sn compound~~, said Cu_3Sn being formed at peripheries of said Cu balls.

1 35. (Previously presented): An electronic device according to claim 34,
2 wherein said Cu-Sn compound is formed by reflowing said Cu-balls and Sn-base solder at a
3 temperature higher than a melting point of said Sn-base solder and lower than a melting point of
4 said Cu-balls.

1 36. (Previously presented): An electronic device according to claim 35,
2 wherein said Sn-base solder comprises eutectic Sn-Cu solder, eutectic Sn-Cu solder to which In,
3 Zn or Bi is added, eutectic Sn-Ag solder, eutectic Sn-Ag solder to which In, Zn or Bi is added,
4 eutectic Sn-Ag-Cu solder or eutectic Sn-Ag-Cu solder to which In, Zn or Bi is added.

1 37. (Previously presented): An electronic device according to claim 35,
2 wherein said Cu-balls have a diameter greater than 5 micrometers.